

<p>FORM 1449*</p> <p>INFORMATION DISCLOSURE STATEMENT</p> <p>IN AN APPLICATION</p> <p>(Use several sheets if necessary)</p> <p><i>SC25</i></p> <p><i>MAR 29 2014</i></p> <p><i>U.S. Patent and Trademark Office</i></p>	Docket Number:	Application Number:
	10873.1333USW1	10/719,412
	Applicant: SUGITA et al.	
	Filing Date: November 21, 2003	Group Art Unit: Unknown

U.S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

 Ji Hyung Yu et al. "Magnetic Tunnel Junctions with High Magnetoresistance and Small Bias Voltage Dependence Using Expitaxial NiFe (111) Ferromagnetic Bottom Electrodes", Journal of Applied Physics, Vol. 93, No.10, pp. 8555-8557, May 15, 2003.

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PATENT TRADEMARK OFFICE

EXAMINER

After Test

DATE CONSIDERED

Feb 10/9

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION <small>(Use several sheets if necessary)</small>			Docket Number: 10873.1333USW1	Application Number: 10/719,412
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EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
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						YES	NO
~	2000-068569	03.2000	Japan			Abstract	
~	2001-236613	08.2001	Japan			Abstract	
~	2000-188435	07.2000	Japan			Abstract	
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~	~	Koichiro INOMATA, MRAM Technology Progress and Prospect" Materials Integration Vol. 13, No. 12, P13-18, 2000 (Japanese only)				
~	~	T.Miyazaki et al., "Giant Magnetic Tunneling Effect in Fe/Al ₂ O ₃ /Fe Junction", Journal of Magnetism and Magnetic Materials, 139 (1995) L231-L234				
~	~	Ping Shang et al., "High-resolution electron microscopy study of tunneling junctions with AlN and Al _{0.9} N barriers", Journal of Applied Physics, Vol. 89, No. 11, pp. 6874-6876, 1 June 2001				
~	~	Yasunari SUGITA et al., "Tunneling Magnetoresistance Enhancement for Pt-Added Magnetic Tunnel Junctions", Japanese Journal of Applied Physics, Vol. 41, No. 10A, pp. L1072-1074, October 1, 2002				
~	~	Nozomu MATSUKAWA et al., "Thermally stable exchange-biased magnetic tunnel junctions over 400° C" Applied Physics Letter, Vol. 81, No. 25, pp. 4784-4786, December 16, 2002				



EXAMINER	<i>H. Jay Saito</i>	DATE CONSIDERED	<i>6/29/04</i>
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